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FGA40N65SMD

650 V, 40 A Field Stop IGBT

August 2014

Features

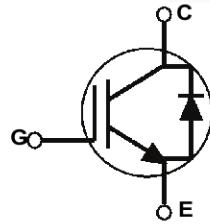
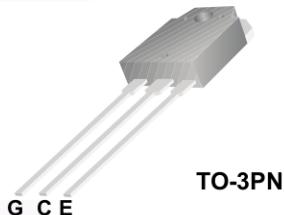
- Maximum Junction Temperature : $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(\text{sat})} = 1.9 \text{ V}(\text{Typ.}) @ I_C = 40 \text{ A}$
- Fast Switching : $E_{\text{OFF}} = 6.5 \text{ uJ/A}$
- Tighten Parameter Distribution
- RoHS Compliant

Applications

- Solar Inverter, UPS, Welder, PFC, Induction Heating
- Telecom, ESS

General Description

Using novel field stop IGBT technology, Fairchild's new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder, induction heating, telecom, ESS and PFC applications where low conduction and switching losses are essential.



Absolute Maximum Ratings

| Symbol | Description | Ratings | Unit |
|------------------|---|-------------|------------------|
| V_{CES} | Collector to Emitter Voltage | 650 | V |
| V_{GES} | Gate to Emitter Voltage | ± 20 | V |
| | Transient Gate to Emitter Voltage | ± 30 | V |
| I_C | Collector Current @ $T_C = 25^\circ\text{C}$ | 80 | A |
| | Collector Current @ $T_C = 100^\circ\text{C}$ | 40 | A |
| $I_{CM(1)}$ | Pulsed Collector Current | 120 | A |
| I_F | Diode Forward Current @ $T_C = 25^\circ\text{C}$ | 40 | A |
| | Diode Forward Current @ $T_C = 100^\circ\text{C}$ | 20 | A |
| $I_{FM(1)}$ | Pulsed Diode Maximum Forward Current | 120 | A |
| P_D | Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ | 349 | W |
| | Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$ | 174 | W |
| T_J | Operating Junction Temperature | -55 to +175 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55 to +175 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds | 300 | $^\circ\text{C}$ |

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

| Symbol | Parameter | Typ. | Max. | Unit |
|-------------------------|---|------|------|------|
| $R_{\theta JC}$ (IGBT) | Thermal Resistance, Junction to Case | - | 0.43 | °C/W |
| $R_{\theta JC}$ (Diode) | Thermal Resistance, Junction to Case | - | 1.5 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | - | 40 | °C/W |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-------------|---------|----------------|-----------|------------|----------|
| FGA40N65SMD | FGA40N65SMD | TO-3PN | Tube | N/A | N/A | 30 |

Electrical Characteristics of the IGBT

$T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|------|------|---------------|
| Off Characteristics | | | | | | |
| BV_{CES} | Collector to Emitter Breakdown Voltage | $V_{GE} = 0 \text{ V}$, $I_C = 250 \mu\text{A}$ | 650 | - | - | V |
| ΔBV_{CES} ΔT_J | Temperature Coefficient of Breakdown Voltage | $V_{GE} = 0 \text{ V}$, $I_C = 250 \mu\text{A}$ | - | 0.6 | - | V/°C |
| I_{CES} | Collector Cut-Off Current | $V_{CE} = V_{CES}$, $V_{GE} = 0 \text{ V}$ | - | - | 250 | μA |
| I_{GES} | G-E Leakage Current | $V_{GE} = V_{GES}$, $V_{CE} = 0 \text{ V}$ | - | - | ±400 | nA |
| On Characteristics | | | | | | |
| $V_{GE(\text{th})}$ | G-E Threshold Voltage | $I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$ | 3.5 | 4.5 | 6.0 | V |
| $V_{CE(\text{sat})}$ | Collector to Emitter Saturation Voltage | $I_C = 40 \text{ A}$, $V_{GE} = 15 \text{ V}$ | - | 1.9 | 2.5 | V |
| | | $I_C = 40 \text{ A}$, $V_{GE} = 15 \text{ V}$, $T_C = 175^\circ\text{C}$ | - | 2.1 | - | V |
| Dynamic Characteristics | | | | | | |
| C_{ies} | Input Capacitance | $V_{CE} = 30 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | - | 1880 | - | pF |
| C_{oes} | Output Capacitance | | - | 180 | - | pF |
| C_{res} | Reverse Transfer Capacitance | | - | 50 | - | pF |
| Switching Characteristics | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{CC} = 400 \text{ V}$, $I_C = 40 \text{ A}$, $R_G = 6 \Omega$, $V_{GE} = 15 \text{ V}$, Inductive Load, $T_C = 25^\circ\text{C}$ | - | 12 | 16 | ns |
| t_r | Rise Time | | - | 20 | 28 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | - | 92 | 120 | ns |
| t_f | Fall Time | | - | 13 | 17 | ns |
| E_{on} | Turn-On Switching Loss | | - | 0.82 | 1.23 | mJ |
| E_{off} | Turn-Off Switching Loss | | - | 0.26 | 0.34 | mJ |
| E_{ts} | Total Switching Loss | | - | 1.08 | 1.57 | mJ |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{CC} = 400 \text{ V}$, $I_C = 40 \text{ A}$, $R_G = 6 \Omega$, $V_{GE} = 15 \text{ V}$, Inductive Load, $T_C = 175^\circ\text{C}$ | - | 15 | - | ns |
| t_r | Rise Time | | - | 22 | - | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | - | 116 | - | ns |
| t_f | Fall Time | | - | 16 | - | ns |
| E_{on} | Turn-On Switching Loss | | - | 1.08 | - | mJ |
| E_{off} | Turn-Off Switching Loss | | - | 0.60 | - | mJ |
| E_{ts} | Total Switching Loss | | - | 1.68 | - | mJ |

Electrical Characteristics of the IGBT (Continued)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max | Unit |
|----------|--------------------------|--|------|------|-----|------|
| Q_g | Total Gate Charge | $V_{CE} = 400$ V, $I_C = 40$ A, $V_{GE} = 15$ V | - | 119 | 180 | nC |
| Q_{ge} | Gate to Emitter Charge | | - | 13 | 20 | nC |
| Q_{gc} | Gate to Collector Charge | | - | 58 | 90 | nC |

Electrical Characteristics of the Diode $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max | Unit |
|-----------|-------------------------------------|---|---------------------------|------|-----|------|
| V_{FM} | Diode Forward Voltage | $I_F = 20$ A | $T_C = 25^\circ\text{C}$ | - | 2.1 | 2.6 |
| | | | $T_C = 175^\circ\text{C}$ | - | 1.7 | - |
| E_{rec} | Reverse Recovery Energy | $I_F = 20$ A, $dI_F/dt = 200$ A/ μs | $T_C = 175^\circ\text{C}$ | - | 96 | - |
| t_{rr} | Diode Reverse Recovery Time | | $T_C = 25^\circ\text{C}$ | - | 42 | - |
| I_{rr} | Diode Peak Reverse Recovery Current | $T_C = 25^\circ\text{C}$ | $T_C = 175^\circ\text{C}$ | - | 200 | - |
| | | | $T_C = 25^\circ\text{C}$ | - | 3.6 | - |
| Q_{rr} | Diode Reverse Recovery Charge | $T_C = 25^\circ\text{C}$ | $T_C = 175^\circ\text{C}$ | - | 8.0 | - |
| | | | $T_C = 25^\circ\text{C}$ | - | 76 | - |
| | | | $T_C = 175^\circ\text{C}$ | - | 800 | - |

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

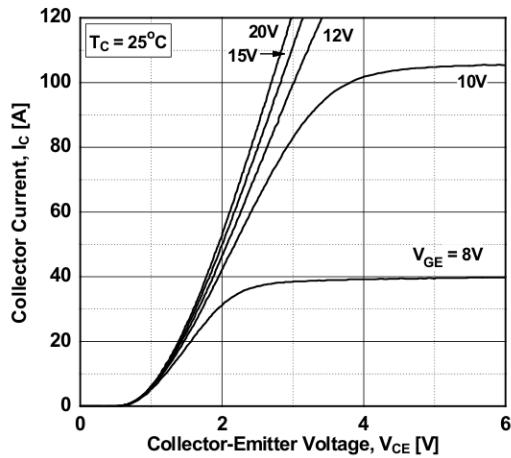


Figure 3. Typical Saturation Voltage Characteristics

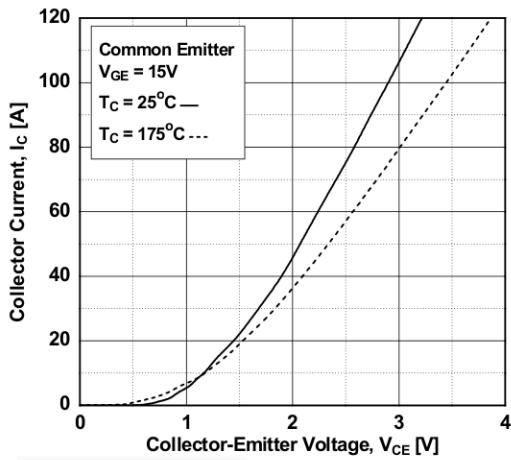


Figure 5. Saturation Voltage vs. V_{GE}

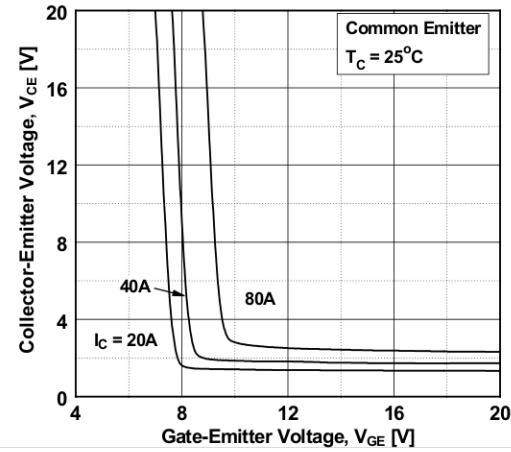


Figure 2. Typical Output Characteristics

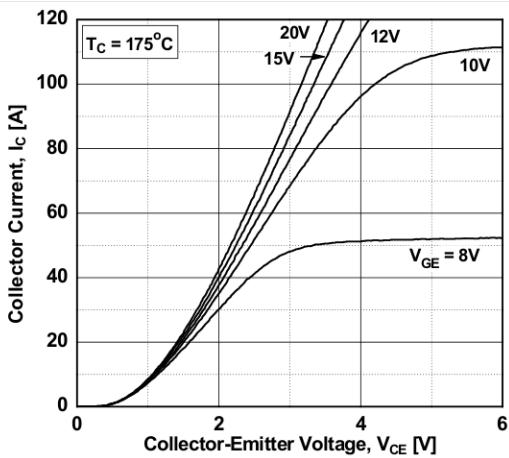


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

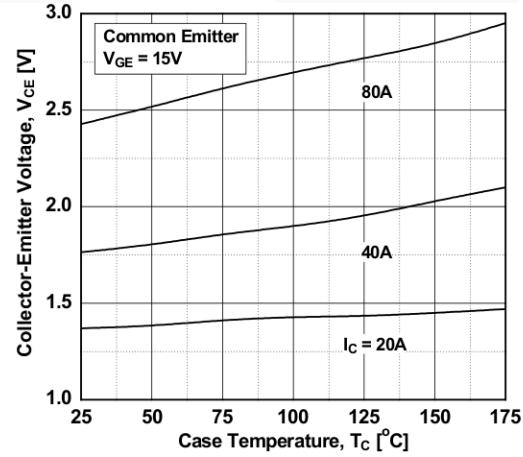
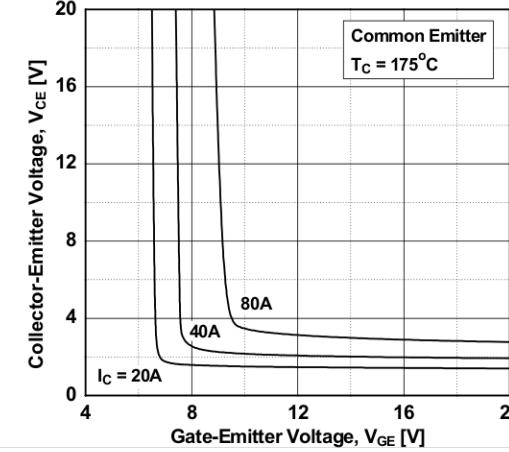


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

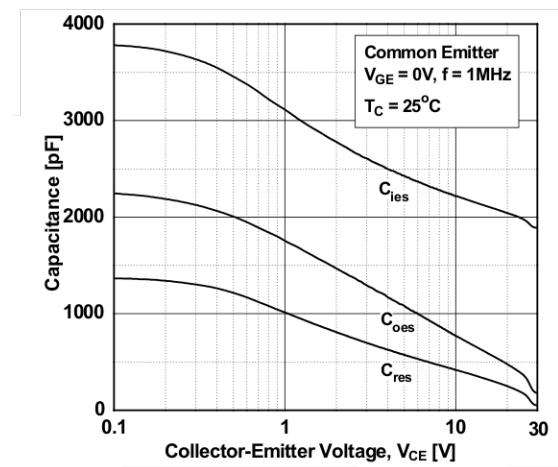


Figure 9. Turn-on Characteristics vs. Gate Resistance

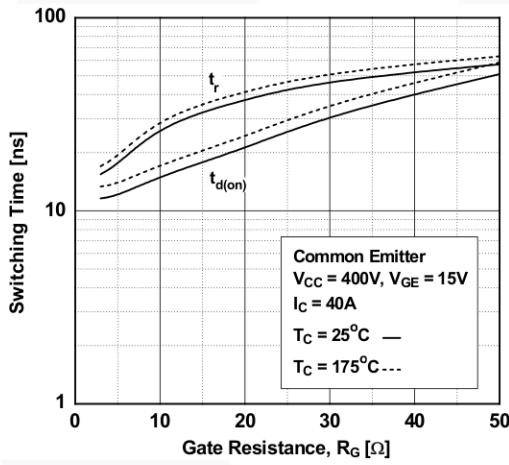


Figure 11. Switching Loss vs. Gate Resistance

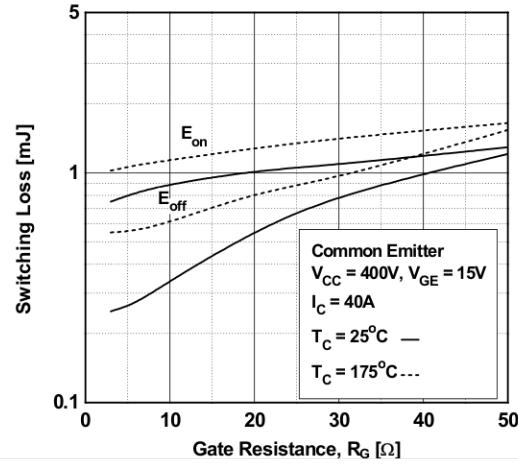


Figure 8. Gate charge Characteristics

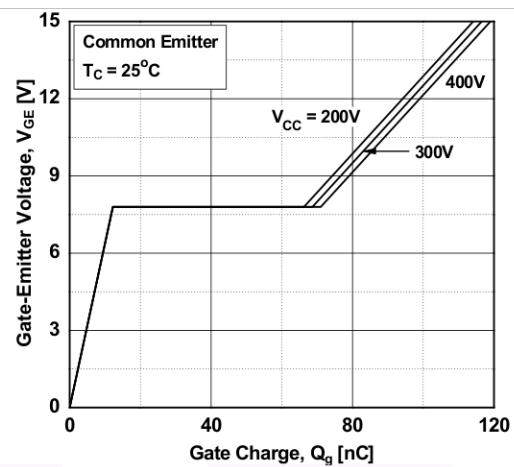


Figure 10. Turn-off Characteristics vs. Gate Resistance

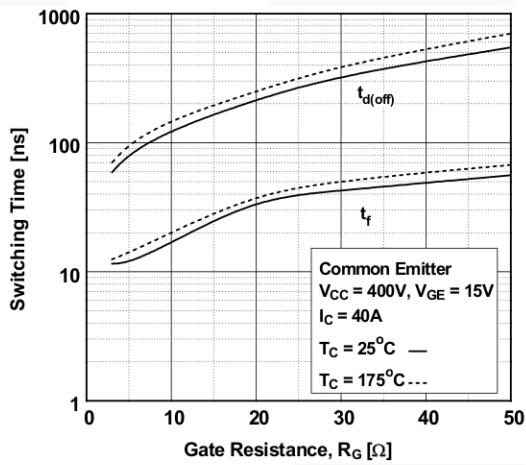
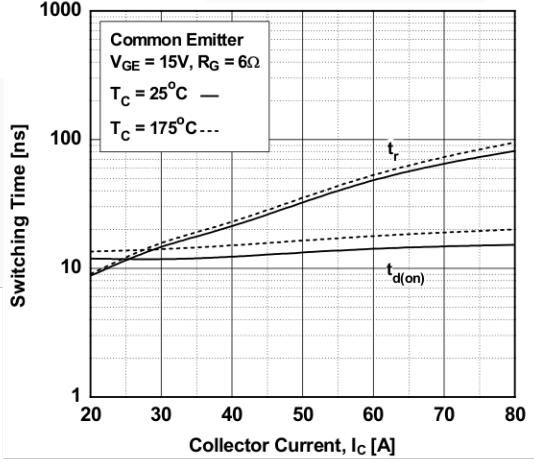


Figure 12. Turn-on Characteristics vs. Collector Current



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

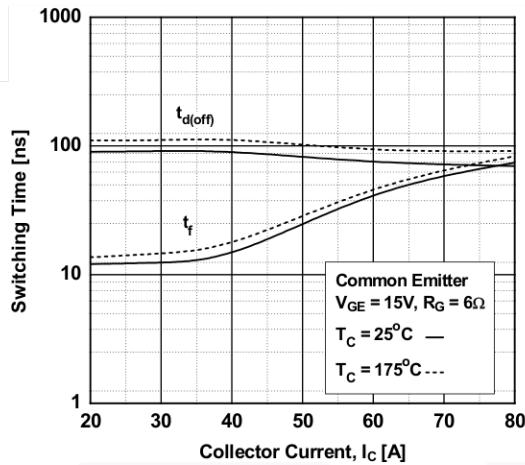


Figure 14. Switching Loss vs. Collector Current

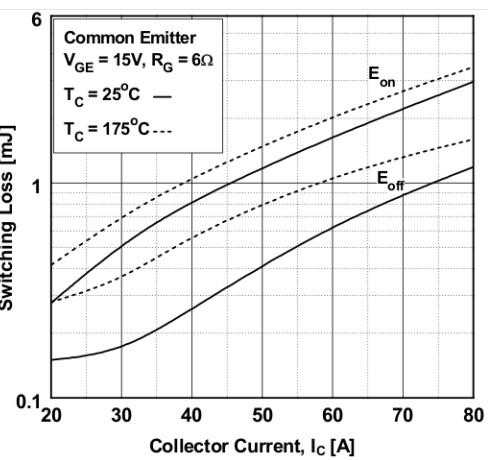


Figure 15. Load Current vs. Frequency

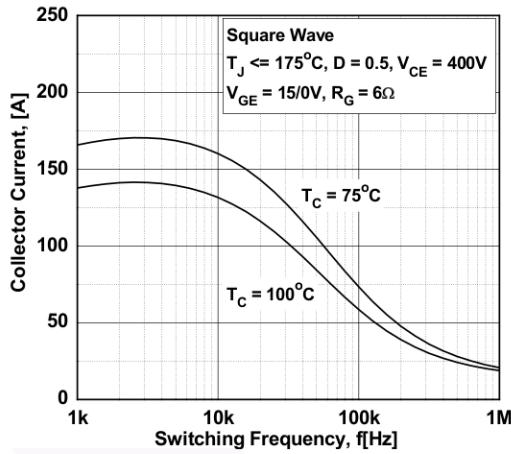


Figure 16. SOA Characteristics

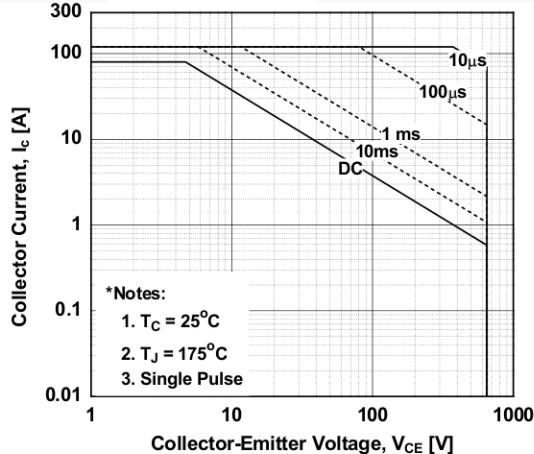


Figure 17. Forward Characteristics

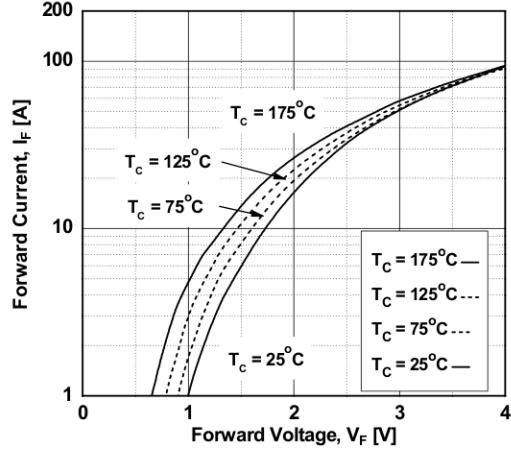
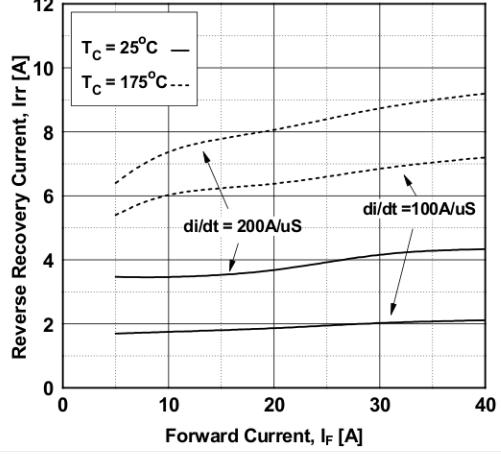


Figure 18. Reverse Recovery Current



Typical Performance Characteristics

Figure 19. Reverse Recovery Time

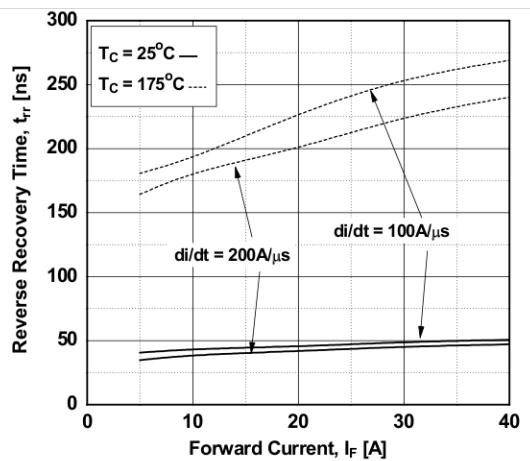


Figure 20. Stored Charge

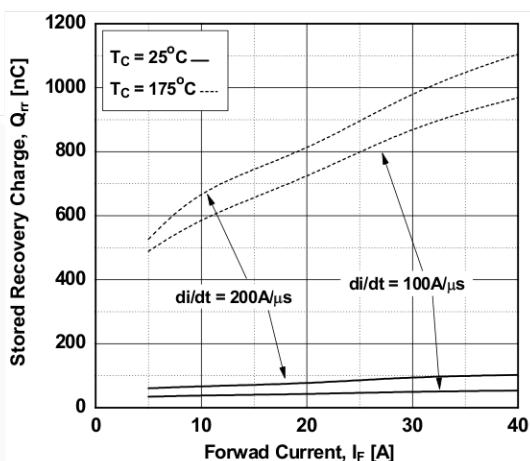


Figure 21. Transient Thermal Impedance of IGBT

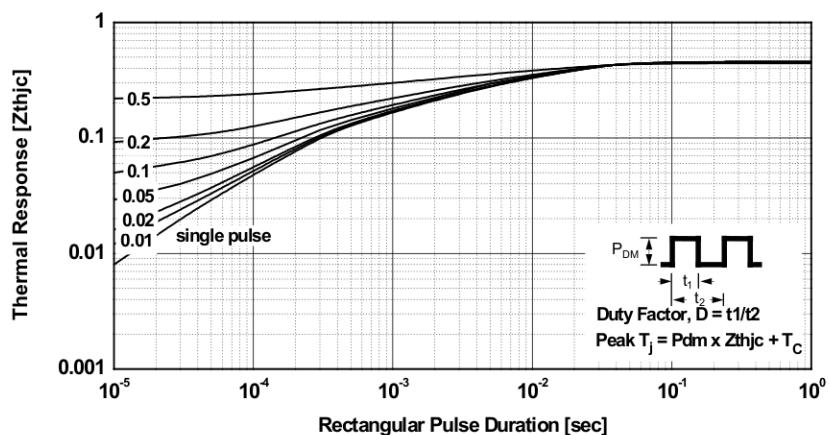
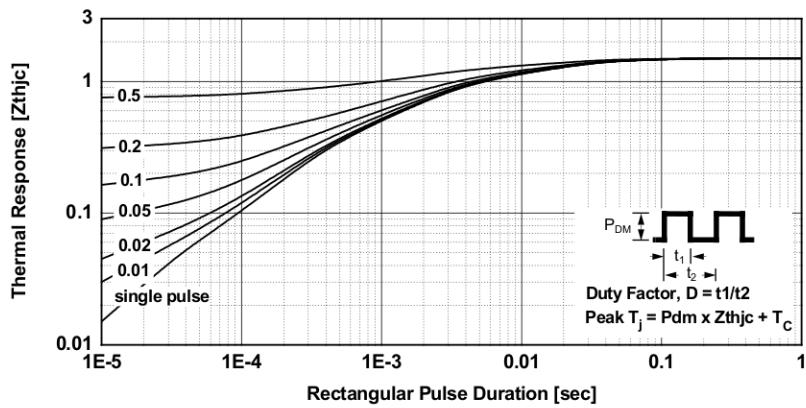
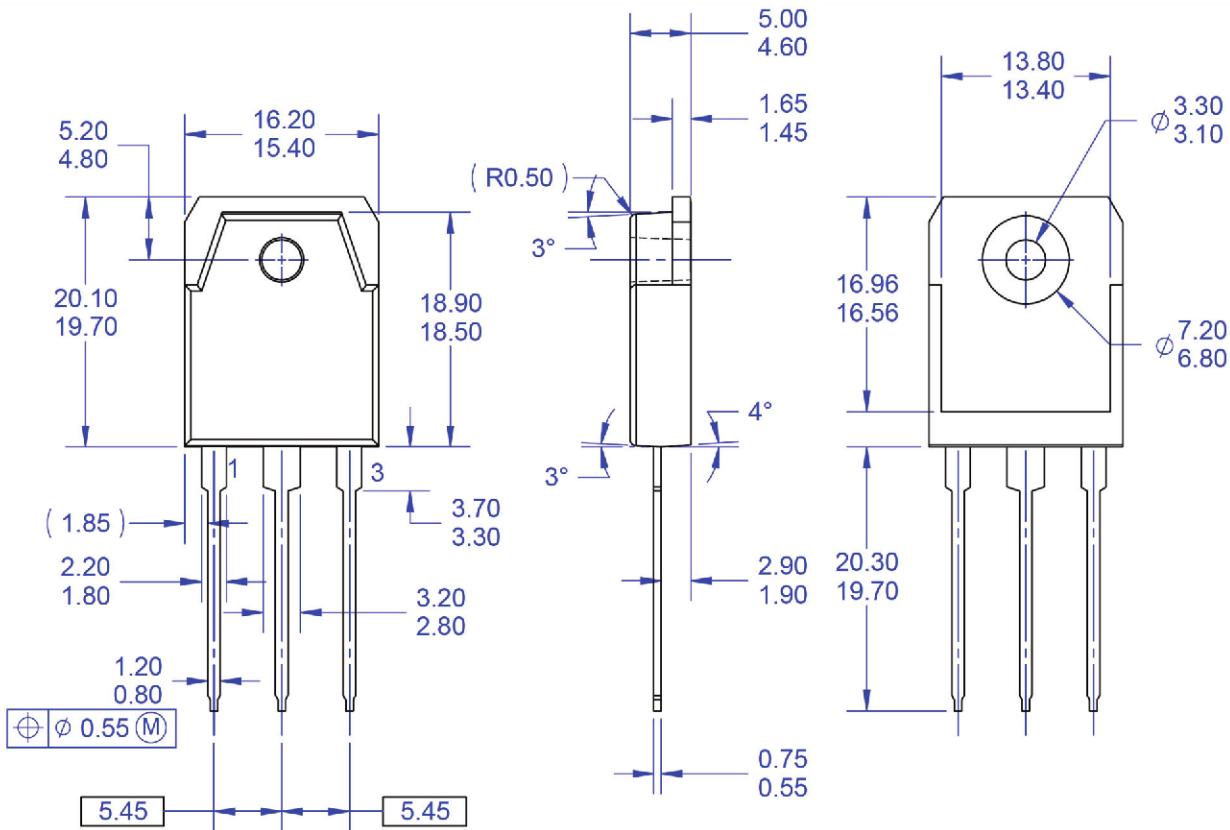


Figure 22. Transient Thermal Impedance of Diode



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

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Figure 23. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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